



FEATURES

Dimensions are in inch [metric] units.

- 40 pin dual in-line package
- Ideal for electron detection
- 100% internal QE

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C (Per Element)

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	2mm x 5mm		10		mm ²
Responsivity, \mathcal{R}	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$		25		Volts
Capacitance, C	$V_R = 0V$			40	pF
Rise Time	$V_R = 0V$		500		nsec
Shunt Resistance (per element)	$V_f = \pm 10mV$	100			MOhms

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ¹	-10° TO 40°C ¹
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead soldering temperature ²	260°C

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



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